

RTE13J1M

Composite Transistor
Zener Diode
Silicon P-channel MOSFET

DESCRIPTION

RTE13J1M is compound transistor built with correspond INJ0001AX chip and 8.2V Zener diode in SC-88 package.

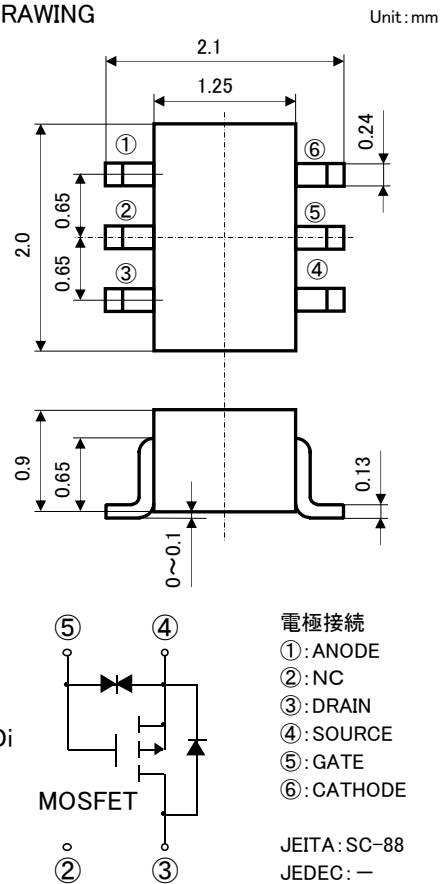
FEATURE

- Silicon epitaxial type
- Each transistor elements are independent.
- Mini package for easy mounting

APPLICATION

Power supply circuit, Driver circuit, etc

OUTLINE DRAWING

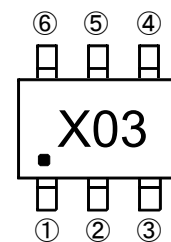


MAXIMUM RATING(T_a=25°C)

SYMBOL	PARAMETER	RATING		UNIT
V _{DSS}	Drain-source voltage	MOSFET	-50	V
V _{GSS}	Gate-source voltage		±8	V
I _D	Drain current(DC)		-100	mA
I _{DP}	Drain current(Pulse)		-400(*1)	mA
P _T	Total power dissipation(T _a =25°C)	MOSFET Di Common	150(*2)	mW
T _j	Junction temperature		+150	°C
T _{stg}	Storage temperature		-55~+150	°C

*1: P_w ≤ 10 μs, Duty cycle ≤ 1% *2: Mounted on glass epoxy board(9mm × 19mm × 1mm)

MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C)

【 MOSFET 】

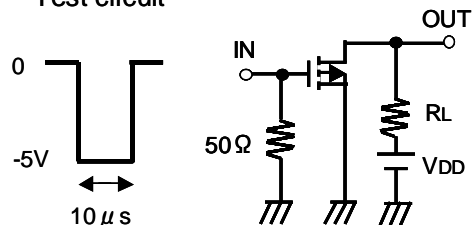
SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
V(BR)DSS	Drain-source breakdown voltage	$I_D = -100 \mu A, V_{GS} = 0V$	-50	-	-	V
I _{GSS}	Gate-source leak current	$V_{GS} = \pm 5V, V_{DS} = 0V$	-	-	± 0.5	μA
I _{DSS}	Zero gate voltage drain current	$V_{DS} = -50V, V_{GS} = 0V$	-	-	-1.0	μA
V _{th}	Gate threshold voltage	$I_D = -250 \mu A, V_{DS} = V_{GS}$	-0.6	-	-1.2	V
Y _{fs}	Forward transfer admittance	$V_{DS} = -10V, I_D = -0.1A$	-	220	-	mS
R _{DS(ON)}	Static drain-source on-state resistance	$I_D = -100mA, V_{GS} = -4.0V$	-	7	-	Ω
C _{iss}	Input capacitance	$V_{DS} = -10V$	-	28	-	pF
C _{oss}	Output capacitance	$V_{GS} = 0V, f = 1MHz$	-	5.2	-	
t _{on}	Switching time	$V_{DD} = -5V, I_D = -10mA$	-	13	-	ns
t _{off}		$V_{GS} = 0 \sim -5V$	-	135	-	

【 Di 】

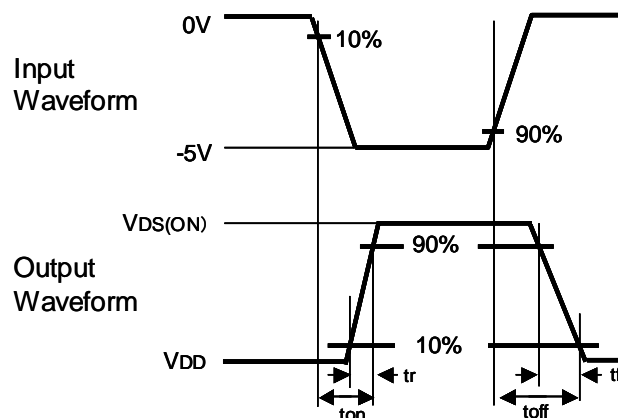
Zener voltage Vz(V)			Reverse current I _R (μA)	
MIN	MAX	I _Z (mA)	MAX	V _R (V)
7.790	8.610	5	0.5	6.5

Switching time test condition

Test circuit



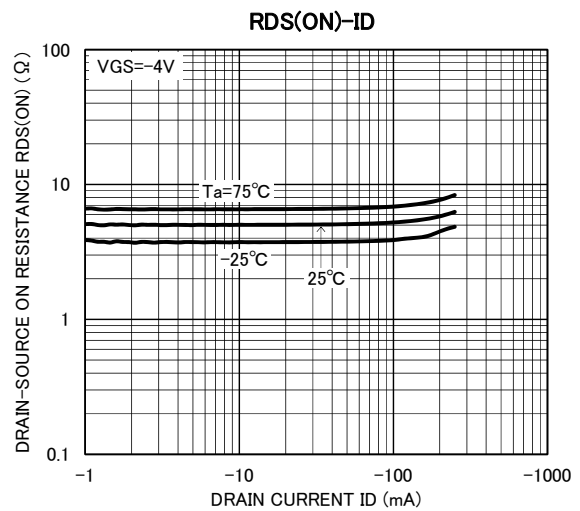
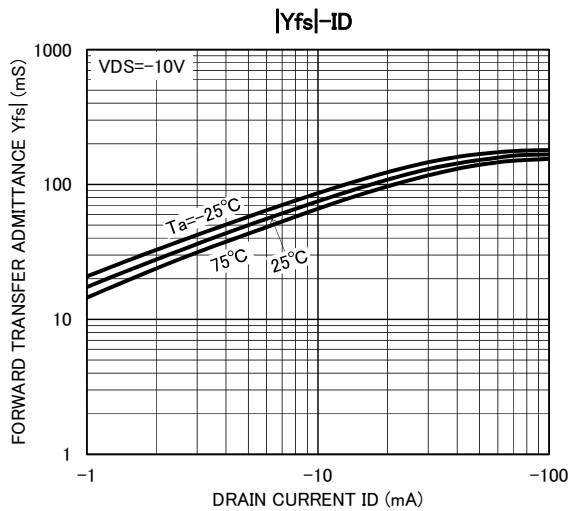
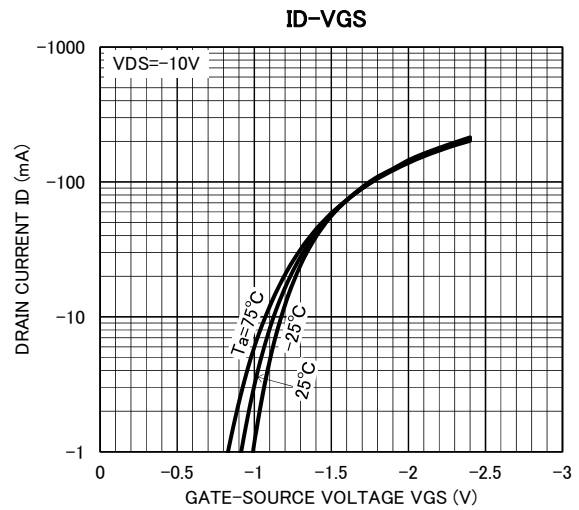
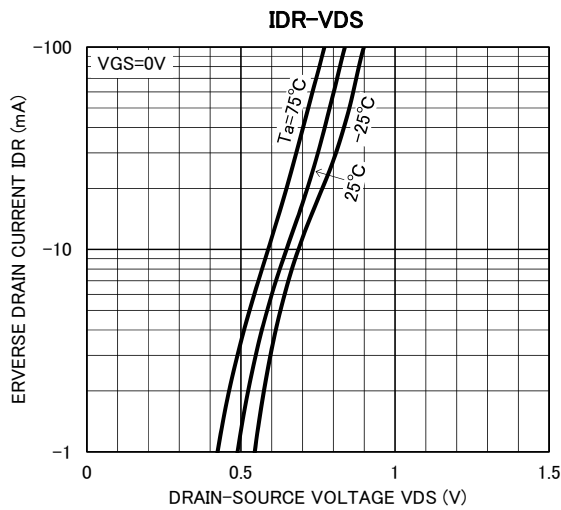
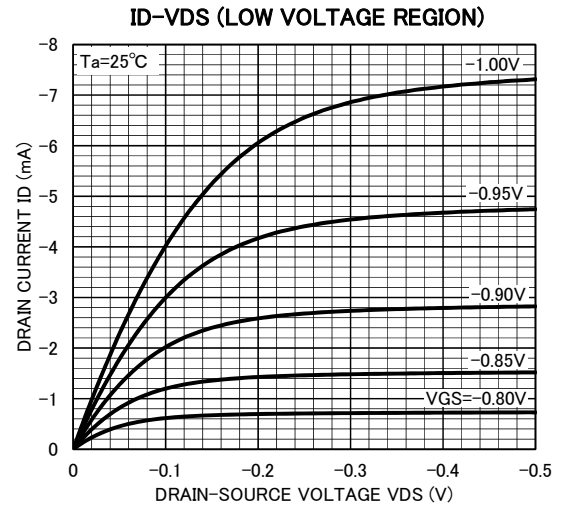
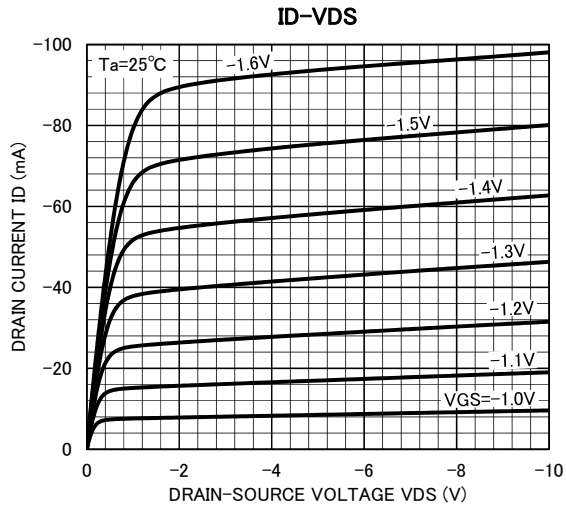
V_{DD} = -5V
Duty ≤ 1%
Common source
Ta = 25°C



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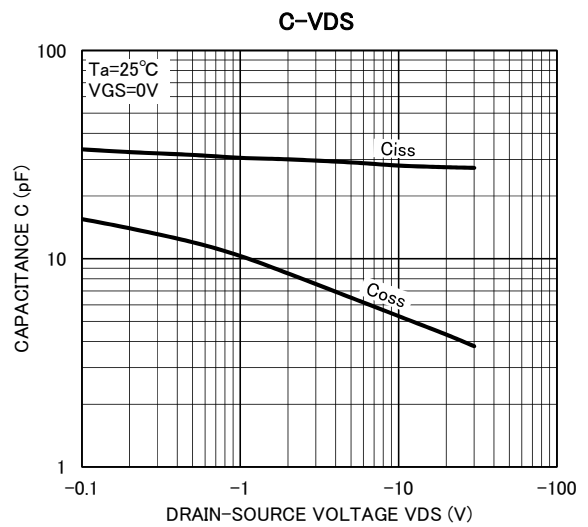
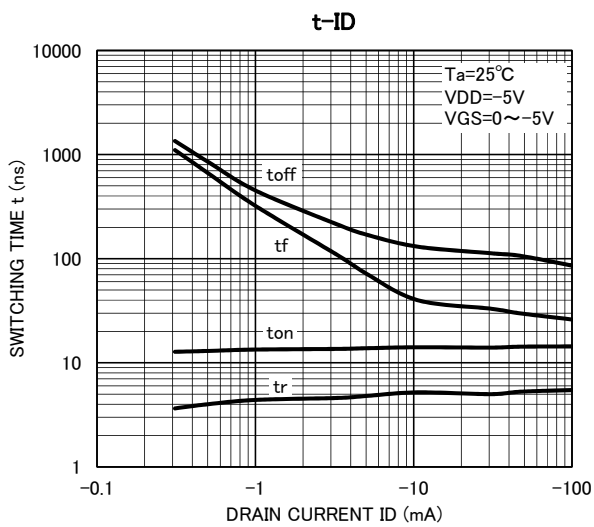
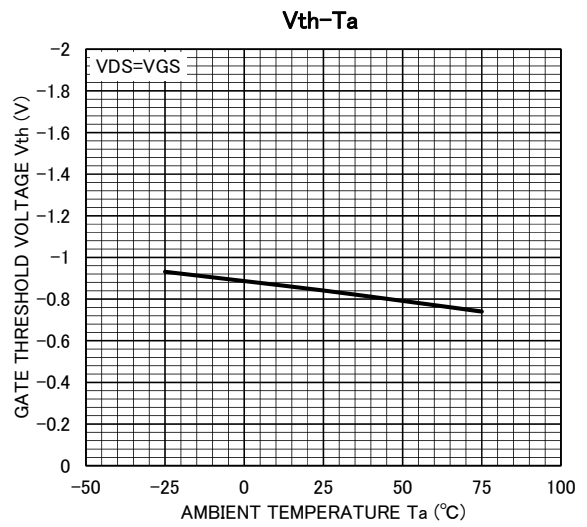
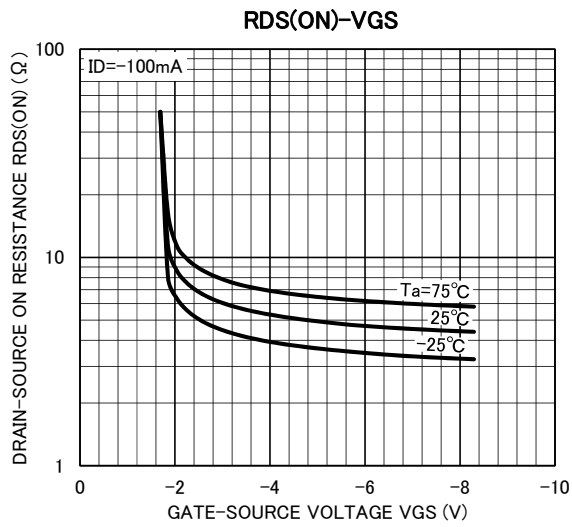
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[MOSFET] TYPICAL CHARACTERISTICS



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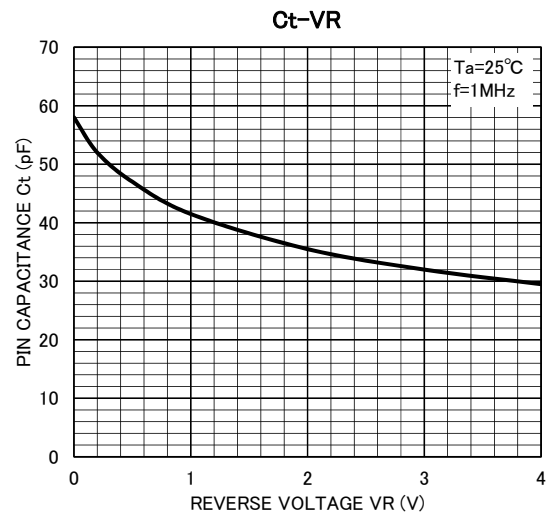
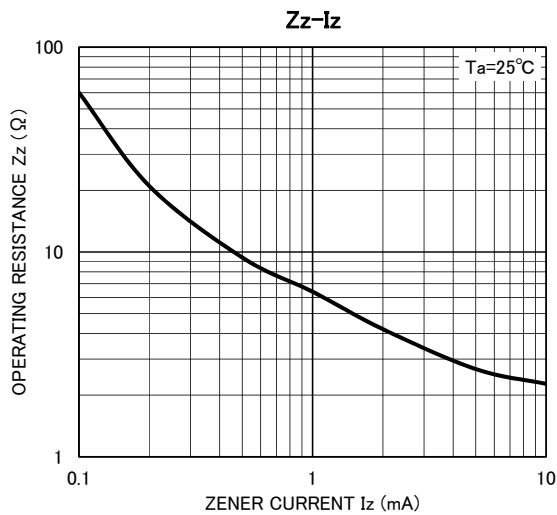
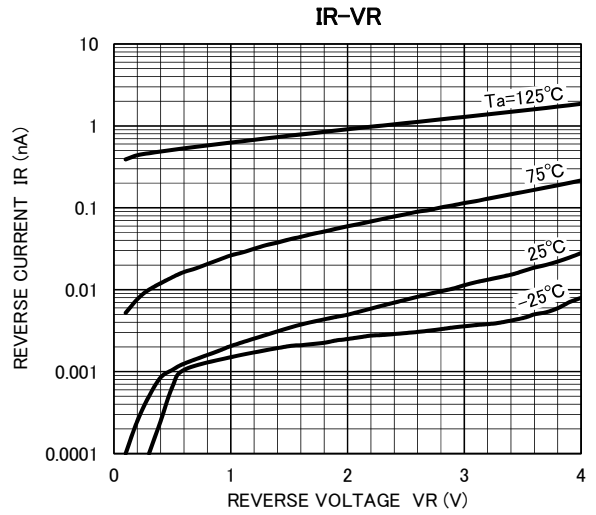
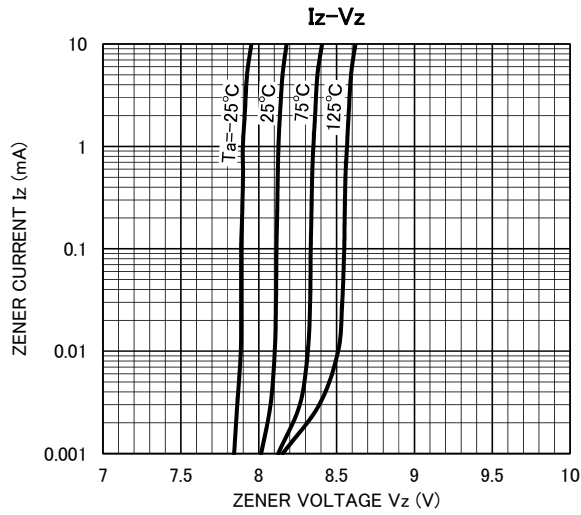
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【Di】TYPICAL CHARACTERISTICS





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